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|-----------------------------------|--|-------------------------|---|-------------|
| <b>Notice of References Cited</b> |  | Application/Control No. | Applicant(s)/Patent Under Reexamination |             |
|                                   |  | 10/700,466              | OHMI, TADAHIRO                          |             |
| Examiner                          |  | Art Unit                |   | Page 1 of 1 |
| Thien F. Tran                     |  | 2811                    |   |             |

**U.S. PATENT DOCUMENTS**

| * | Document Number<br>Country Code-Number-Kind Code | Date<br>MM-YYYY | Name | Classification |
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**NON-PATENT DOCUMENTS**

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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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